

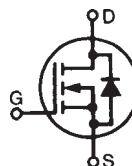
PolarHV™ HiPerFET IXFR 44N50P

Power MOSFET

ISOPLUS247™

(Electrically Isolated Back Surface)

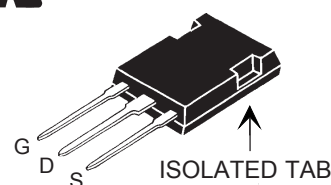
N-Channel Enhancement
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 24 \text{ A} \\ R_{DS(on)} &\leq 150 \text{ m}\Omega \\ t_{rr} &\leq 200 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	500	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GSM}	Transient	± 40	V
V_{GSM}	Continuous	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	24	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	132	A
I_{AR}	$T_C = 25^\circ\text{C}$	44	A
E_{AR}	$T_C = 25^\circ\text{C}$	55	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.7	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 10 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	208	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS, 1 minute	2500	V~
F_c	Mounting Force	20..120 / 4.5..25	N/lb
Weight		5	g

ISOPLUS247 (IXFR)
E153432



G = Gate
S = Source
D = Drain

Features

- International standard isolated package
- UL recognized package
- Silicon chip on Direct-Copper-Bond substrate
 - High power dissipation
 - Isolated mounting surface
 - 2500V electrical isolation
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic diode

Advantages

- Easy to mount
- Space savings
- High power density

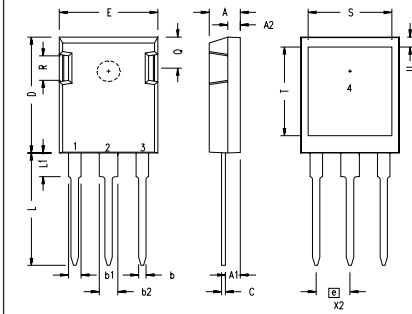
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$			25 μA 500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 22 \text{ A}$			150 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}$; $I_D = 22\text{ A}$, Note 1		32	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		5440	pF
C_{oss}			639	pF
C_{rss}			40	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 22\text{ A}$ $R_G = 3\ \Omega$ (External)		25	ns
t_r			27	ns
$t_{d(off)}$			70	ns
t_f			18	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 22\text{ A}$		98	nC
Q_{gs}			35	nC
Q_{gd}			30	nC
R_{thJC}		0.15		$0.6\ ^\circ\text{C/W}$
R_{thCS}				$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			30 A
I_{SM}	Repetitive			132 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = 22\text{ A}$,			200 ns
Q_{RM}	$-di/dt = 100\text{ A}/\mu\text{s}$		0.6	μC
I_{RM}	$V_R = 100\text{ V}$		6.0	A

Notes: 1. Pulse test, $t \leq 300\text{ ms}$, duty cycle $d \leq 2\%$

ISOPLUS247 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

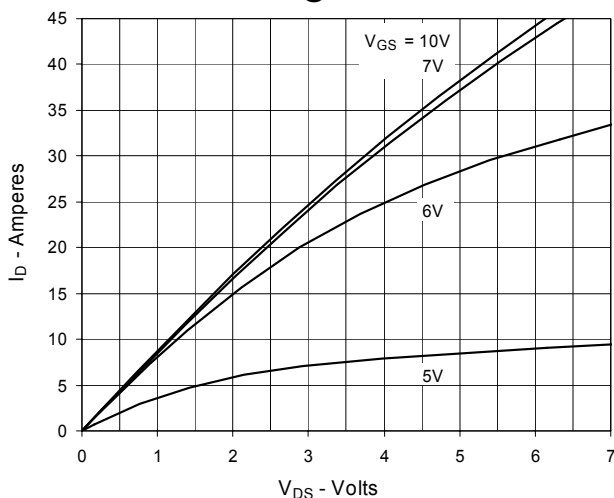
- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

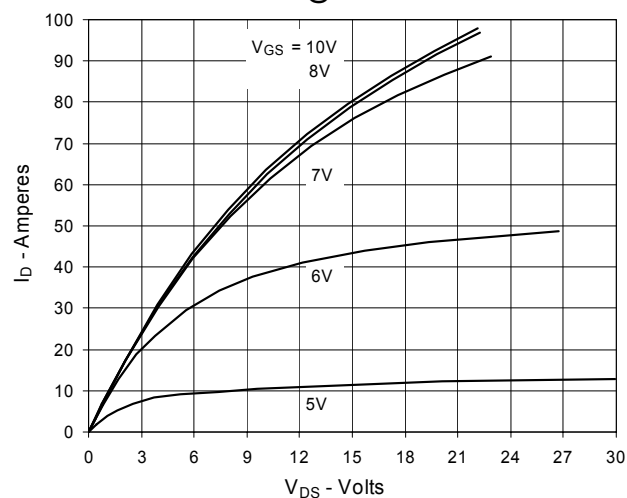
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

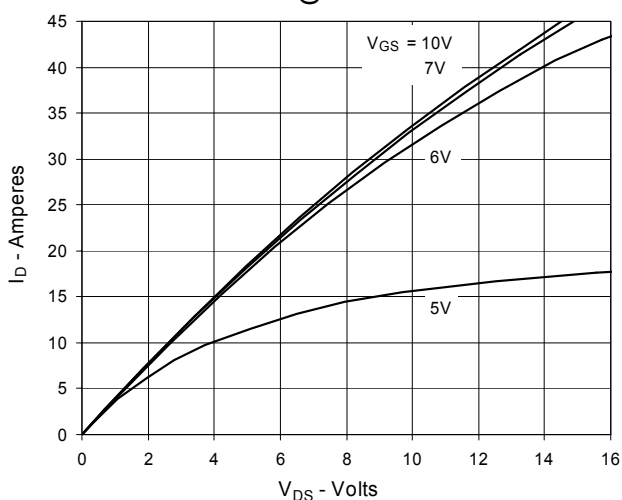
**Fig. 1. Output Characteristics
@ 25°C**



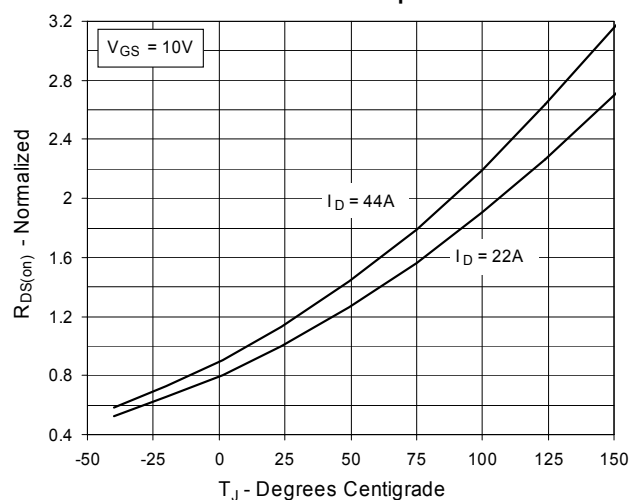
**Fig. 2. Extended Output Characteristics
@ 25°C**



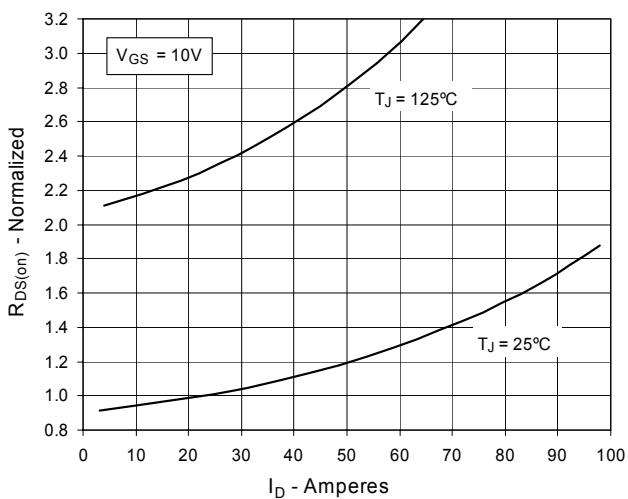
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 22A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 22A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

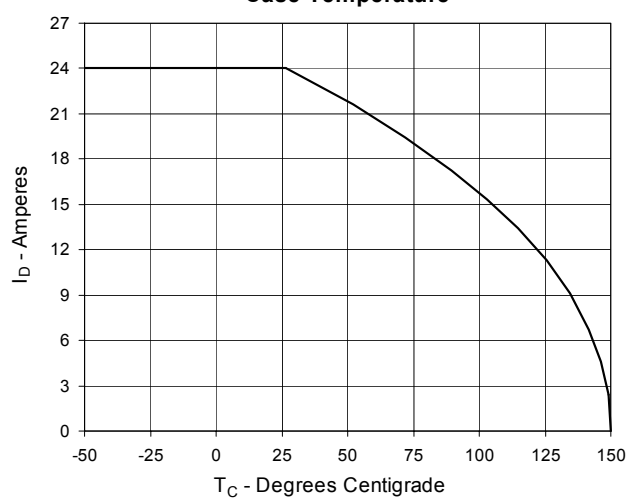


Fig. 7. Input Admittance

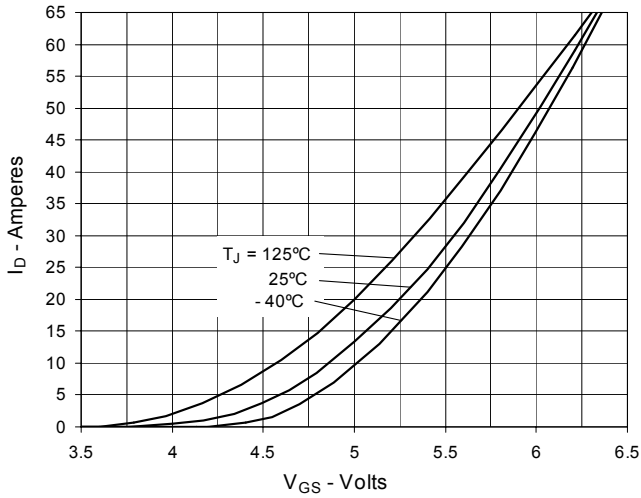


Fig. 8. Transconductance

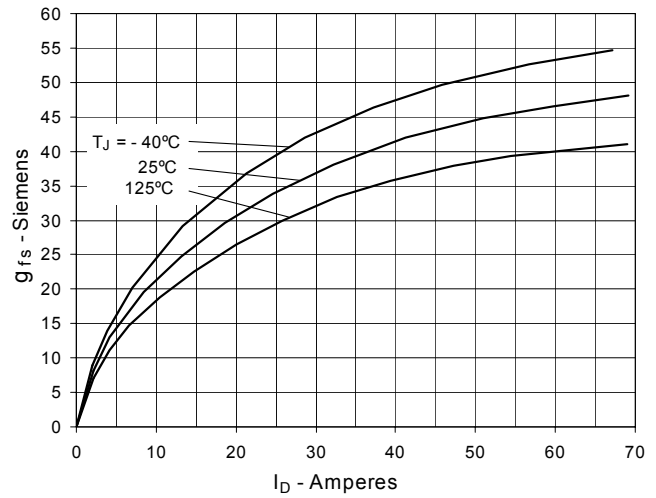


Fig. 9. Forward Voltage Drop of Intrinsic Diode

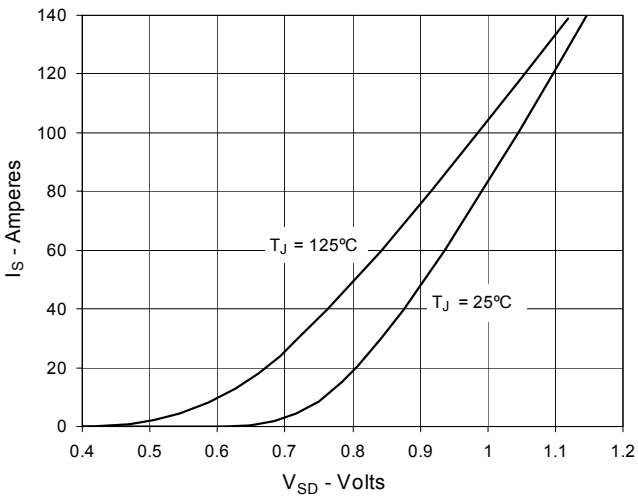


Fig. 10. Gate Charge

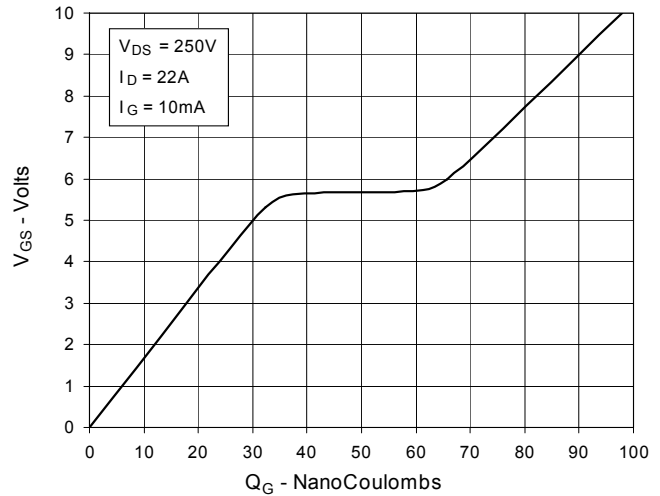


Fig. 11. Capacitance

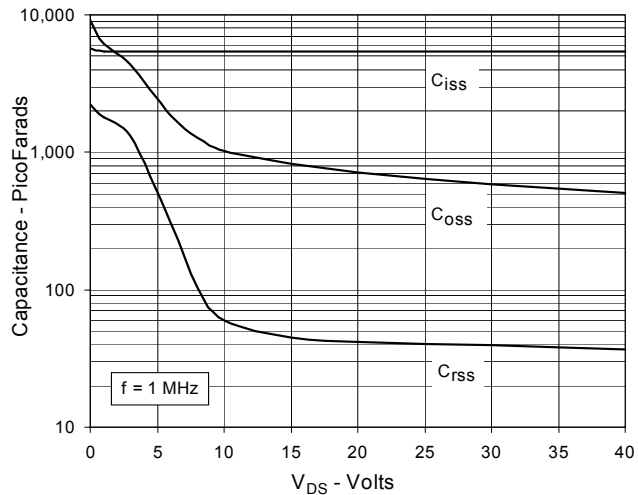


Fig. 12. Forward-Bias Safe Operating Area

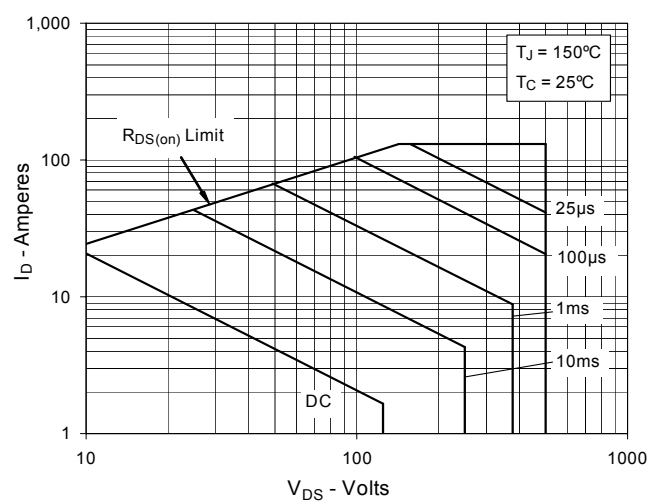
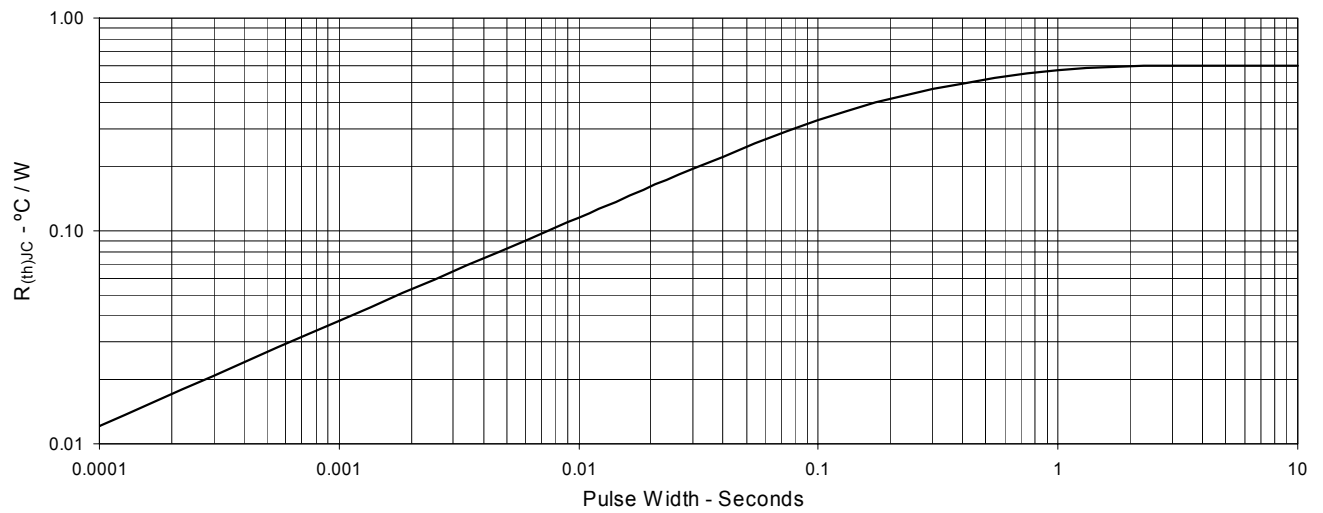


Fig. 13. Maximum Transient Thermal Resistance





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